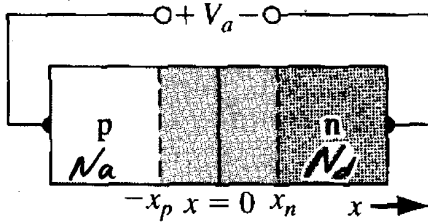


- 8.16** Consider an ideal silicon pn junction diode with the geometry shown in Figure P8.16. The doping concentrations are $N_a = 5 \times 10^{16} \text{ cm}^{-3}$ and $N_d = 1.5 \times 10^{16} \text{ cm}^{-3}$, and the minority carrier lifetimes are $\tau_{n0} = 2 \times 10^{-7} \text{ s}$ and $\tau_{p0} = 8 \times 10^{-8} \text{ s}$. The cross-sectional area is $A = 5 \times 10^{-4} \text{ cm}^2$. Calculate (a) the ideal reverse-saturation current due to holes, (b) the ideal reverse-saturation current due to electrons, (c) the hole concentration at $x = x_n$ for $V_a = 0.8V_{bi}$, (d) the electron current at $x = x_n$ for $V_a = 0.8V_{bi}$, and (e) the electron current at $x = x_n + (1/2)L_p$ for $V_a = 0.8V_{bi}$.

- First, calculate the minority thermal equilibrium carrier concentrations and diffusion lengths for the n & p regions.



From Table B.4 & p. 323

$$n_i = 1.5 \times 10^{10} \text{ cm}^{-3} = 1.5 \times 10^{16} \text{ m}^{-3},$$

$$@ 300\text{K } D_p = 10 \frac{\text{cm}^2}{\text{s}}, + D_n = 25 \frac{\text{cm}^2}{\text{s}}$$

n region $n_{n0} \approx N_d = 1.5 \times 10^{16} \text{ cm}^{-3} = 1.5 \times 10^{22} \text{ m}^{-3}$

$$(4.43) p_{n0} = \frac{n_i^2}{n_{n0}} = \frac{(1.5 \times 10^{10})^2}{1.5 \times 10^{16}} = \underline{\underline{1.5 \times 10^4 \text{ cm}^{-3} = 1.5 \times 10^{10} \text{ m}^{-3}}}$$

$$(6.63) L_n = \sqrt{D_n \tau_{n0}} = \sqrt{25(2 \times 10^{-7})} = \underline{\underline{0.002236 \text{ cm} = 2.236 \times 10^{-5} \text{ m}}}$$

p region $p_{p0} \approx N_a = 5 \times 10^{16} \text{ cm}^{-3} = 5 \times 10^{22} \text{ m}^{-3}$

$$(4.43) n_{p0} = \frac{n_i^2}{p_{p0}} = \frac{(1.5 \times 10^{10})^2}{5 \times 10^{16}} = \underline{\underline{4.5 \times 10^3 \text{ cm}^{-3} = 4.5 \times 10^9 \text{ m}^{-3}}}$$

$$(8.9) L_p = \sqrt{D_p \tau_{p0}} = \sqrt{10(8 \times 10^{-8})} = \underline{\underline{0.0008944 \text{ cm} = 8.94427 \times 10^{-6} \text{ m}}}$$

$$a) (8.26) J_s = \underbrace{\frac{e D_p p_{n0}}{L_p}}_{\text{holes}} + \underbrace{\frac{e D_n n_{p0}}{L_n}}_{\text{electrons}}$$

$$J_{s,p} = \frac{1.6021766 \times 10^{-19} (10) 1.5 \times 10^4}{0.0008944} = 2.68693 \times 10^{-11} \text{ A/cm}^2$$

$$I_{s,p} = J_{s,p} (A) = 2.6869 \times 10^{-11} (5 \times 10^{-4}) = \underline{\underline{1.3435 \times 10^{-14} \text{ A}}}$$

$$b) \quad J_{S,n} = \frac{1.6021766 \times 10^{-19} (25) 4.5 \times 10^3}{0.002236} = 8.0608 \times 10^{-12} \text{ A/cm}^2$$

$$I_{S,n} = J_{S,n}(A) = 8.0608 \times 10^{-12} (5 \times 10^{-4}) = \underline{\underline{4.0304 \times 10^{-15} \text{ A}}}$$

c) First, find V_{bi} using (7.10)

$$V_{bi} = \frac{k_B T}{e} \ln \left(\frac{N_A N_D}{n_i^2} \right) = \frac{8.617333 \times 10^{-5} \text{ eV/K} (300\text{K})}{e} \ln \left(\frac{5 \times 10^{16} (1.5 \times 10^{16})}{(1.5 \times 10^{10})^2} \right)$$

\downarrow
0.025852

$$= 0.745442 \text{ V}$$

$$V_a = 0.8 V_{bi} = 0.8 (0.745442) = 0.5963538 \text{ V}$$

Per (8.11a), $p_n(x_n) = p_{n0} e^{V_a / k_B T / e}$

$$= 1.5 \times 10^4 \text{ cm}^{-3} e^{\frac{0.5963538}{0.025852}}$$

$$\underline{\underline{p_n(x_n) = 1.56457 \times 10^{14} \text{ cm}^{-3} = 1.565 \times 10^{20} \text{ m}^{-3}}}$$

d) Per (8.24), $J_n(-x_p) = \frac{e D_n n_{p0}}{L_n} \left[e^{V_a / k_B T / e} - 1 \right]$

\downarrow
 $J_{S,n}$ (part b)

Since current is continuous across depletion layer $J_n(x_n) = J_n(-x_p)$

$$J_n(x_n) = 8.0608 \times 10^{-12} \text{ A/cm}^2 \left[e^{\frac{0.5963538}{0.025852}} - 1 \right]$$

$$= 0.0840777 \text{ A/cm}^2$$

$$I_n(x_n) = J_n(x_n) A = 0.0840777 (5 \times 10^{-4})$$

$$\underline{\underline{I_n(x_n) = 4.20389 \times 10^{-5} \text{ A} = 42.0389 \mu\text{A}}}$$

e) The total diode current $I = I_n(x_p) + I_p(x_n) = J(A)$

$$\begin{aligned} \text{where (8.26)} \quad J_s &= \frac{e D_p p_{n0}}{L_p} + \frac{e D_n n_{p0}}{L_n} \quad \left. \begin{array}{l} \text{use a) \& b)} \\ \text{results} \end{array} \right\} \\ &= 2.68693 \times 10^{-11} + 8.0608 \times 10^{-12} \\ &= 3.49301 \times 10^{-11} \text{ A/cm}^2 \end{aligned}$$

$$\begin{aligned} \text{per (8.27)} \quad J &= J_s \left[e^{V_a/k_B T/e} - 1 \right] \\ &= 3.49301 \times 10^{-11} \left[e^{\frac{0.5963538}{0.025852}} - 1 \right] \\ &= 0.364337 \text{ A/cm}^2 \end{aligned}$$

$$I = J(A) = 0.364337 (5 \times 10^{-4}) = 1.82168 \times 10^{-4} \text{ A}$$

To get the electron current (majority carriers), we will subtract the minority current (holes) from the total current I .

$$\text{Per (8.28), } J_p(x) = \frac{e D_p p_{n0}}{L_p} \left[e^{V_a/k_B T/e} - 1 \right] e^{-\frac{x_n - x}{L_p}}$$

$$\begin{aligned} J_p(x_n + L_p/2) &= 2.68693 \times 10^{-11} \left[e^{\frac{0.5963538}{0.025852}} - 1 \right] e^{-\frac{x_n - x_n - L_p/2}{L_p}} \\ &= 0.280259 e^{-1/2} = 0.169986 \text{ A/cm}^2 \end{aligned}$$

$$\begin{aligned} I_p(x_n + L_p/2) &= J_p(x_n + L_p/2) A = 0.169986 (5 \times 10^{-4}) \\ &= 8.49929 \times 10^{-5} \text{ A} \end{aligned}$$

$$I_n(x_n + L_p/2) = I - I_p(x_n + L_p/2) = 1.82168 \times 10^{-4} - 8.4993 \times 10^{-5}$$

$$\underline{\underline{I_n(x_n + L_p/2) = 9.71755 \times 10^{-5} \text{ A} = 97.176 \mu\text{A}}}$$